

Gallium Arsenide Tuning Varactors

This range of epitaxial GaAs Schottky barrier variable capacitance diodes is designed primarily for electronic tuning of Gunn and transistor microwave oscillators. They have the advantage over silicon tuning diodes in that the required change in capacitance occurs over a lower tuning voltage range and, as such, is more compatible with Gunn and transistor power supplies. GaAs varactors also exhibit excellent low noise characteristics.

The total capacitance includes the encapsulation capacitance which is approximately 0.25 pF for outline 00, and 0.08 pF for outline 20. Diodes can be supplied to smaller total capacitance spreads to special order.

	Minimum working voltage (V)	Total capacitance (pF)	Typical capacitance ratio		Typical quality factor at	Outling
Туре			0-20 V	0-30 V	0 V, 10 GHz (Q)	Outline (see page 13)
DC4301A DC4302A DC4303A DC4304A DC4305A	20	2.2 1.3 0.8 3.3 4.7	4.5	-	4.3 6.0 6.6 3.4 3.3	00
DC4301B DC4302B DC4303B DC4304B DC4305B	30	2.2 1.3 0.8 3.3 4.7	4.5	6.0	4.3 6.0 6.6 3.4 3.3	00
DC4371A DC4372A DC4373A DC4374A DC4375A	20	2.2 1.3 0.8 3.3 4.7	4.5	_	4.3 6.0 6.6 3.4 3.3	20
DC4371B DC4372B DC4373B DC4374B DC4375B	30	2.2 1.3 0.8 3.3 4.7	4.5	6.0	4.3 6.0 6.6 3.4 3.3	20



Outline 20, 20 X actual size



Outline 00, 10 X actual size